

### **REMARKS/ARGUMENTS**

The applicant's attorneys appreciate the Examiner's thorough search and remarks.

Claim 10 has been canceled.

Claim 9 has been rejected over Floyd '716 (of record) in view of Love, U.S. Patent No. 4,516,143 or Bulucea et al. U.S. Patent No. 5,701,023.

Claim 9 has been amended to call for the following combination:

9. A power MOSFET having reduced on resistance comprising:

a P+ conductivity substrate; an epitaxially deposited N+ conductivity layer deposited atop said P+ substrate to form an epitaxial layer having a substantially uniform concentration of N type dopants throughout its volume; a plurality of spaced stripe trenches having vertical walls extending through said epitaxial layer into said P+ conductivity substrate; a thin gate oxide on said vertical walls and conductive polysilicon with a P type conductivity deposited into said trenches to define a polysilicon gate; P+ concentration source region stripes formed adjacent the walls of each of said trenches and diffused into the top of said epitaxial layer; a plurality of spaced notches extending through said source regions and exposing said epitaxially deposited layer; an N++ region formed in said N+ epitaxially deposited layer at bottom of each notch; a source contact connected to at least said source regions; and a drain contact made of metal and connected to a bottom surface of said substrate, wherein the doping of said N++ epitaxially deposited layer allows reverse voltage to be blocked therein and wherein said source contact extends through said plurality of notches and is connected to each said N++ region.

Claim 9 relates to a power MOSFET which includes an N+ type epitaxially body (serving as the base region of the device).

On the other hand, Floyd '716 teaches a process for fabricating an INV FET that includes P conductivity base region 24 or an ACCUFET N-base region 24A.

Furthermore, claim 9 calls for P+ source region stripes and spaced stripe trenches.

Moreover, claim 9 calls for N++ regions formed in the N+ epitaxial layer at the bottom of notches that extend through the source regions to which a source contact is coupled.

Floyd does not teach or suggest the combination of limitations set forth in claim 9.

Love and Bulucea also fail to teach or suggest the features set forth in claim 9.

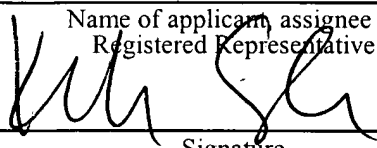
It is respectfully submitted, therefore, that the art of record fails to render claim 9 obvious. Reconsideration is requested.

The application is believed to be in condition for allowance. Such action is earnestly solicited.

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Mail Stop Amendment, Commissioner of Patents and Trademarks, P.O. Box 1450, Alexandria, VA 22313-1450, on April 24, 2008

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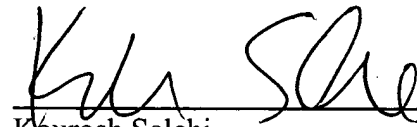
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April 24, 2008

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Respectfully submitted,



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